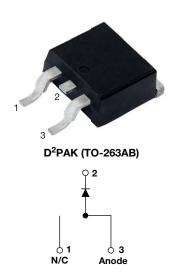


HALOGEN

FREE

HEXFRED®, Ultrafast Soft Recovery Diode, 4 A



PRIMARY CHARACTERISTICS						
I _{F(AV)}	4 A					
V_{R}	600 V					
V _F at I _F	1.4 V					
t _{rr} (typ.)	17 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single					

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		600	V				
Maximum continuous forward current	I _F	T _C = 100 °C	4					
Single pulse forward current	I _{FSM}		25	Α				
Maximum repetitive forward current	I _{FRM}		16					
Maximum newer discination	P _D	T _C = 25 °C	25	W				
Maximum power dissipation		T _C = 100 °C	10	VV				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100 \mu A$		600	1	-		
		$I_F = 4.0 \text{ A}$		-	1.5	1.8	v	
Maximum forward voltage	V_{FM}	$I_F = 8.0 \text{ A}$	See fig. 1 - 1.	1.8	2.2	v		
		I _F = 4.0 A, T _J = 125 °C		1	1.4	1.7		
Maximum reverse leakage current	I	$V_R = V_R$ rated	See fig. 2	-	0.17	3.0		
Waximum reverse leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	44	300	μA	
Junction capacitance	C _T	V _R = 200 V See fig. 3		1	4.0	8.0	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -				nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CON	IDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	Vμs, V _R = 30 V	-	17	-			
Reverse recovery time See fig. 5, 6	t _{rr1}	T _J = 25 °C		-	28	42	ns		
330 lig. 5, 5	t _{rr2}	T _J = 125 °C		-	38	57			
Dook room ourrent	I _{RRM1}	T _J = 25 °C		-	2.9	5.2	A		
Peak recovery current	I _{RRM2}	T _J = 125 °C	$I_F = 4.0 \text{ A}$ $di_F/dt = 200 \text{ A/}\mu\text{s}$	-	3.7	6.7			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	40	60	nC		
See fig. 7	Q _{rr2}	T _J = 125 °C		=.	70	105	IIC		
Peak rate of fall of recovery current	di _{(rec)M} /dt1	T _J = 25 °C		-	280	-	A/μs		
during t _b , see fig. 8	di _{(rec)M} /dt2	T _J = 125 °C		-	235	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction-to-case	R_{thJC}		-	-	5.0	K/W			
Thermal resistance, junction-to-ambient	R_{thJA}	Typical socket mount	-	-	80	IV VV			
Weight			-	2.0	-	g			
vveignt			-	0.07	-	oz.			
Marking device		Case style D ² PAK (TO-263AB)	HFA04TB60S						

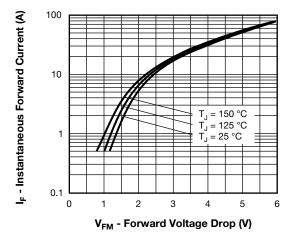


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

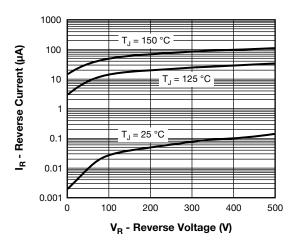


Fig. 2 - Typical Reverse Current vs. Reverse Voltage



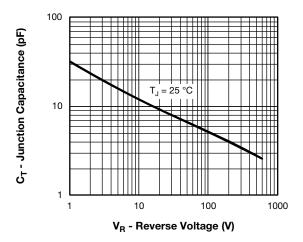


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

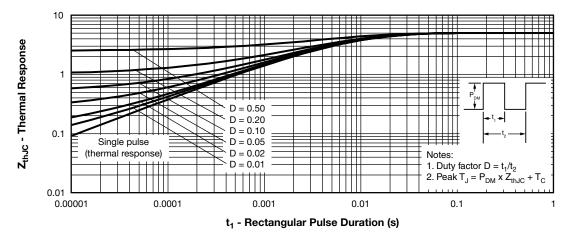


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

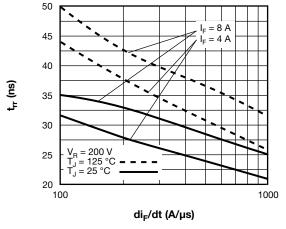


Fig. 5 - Typical Reverse Recovery Time vs. di_F/dt

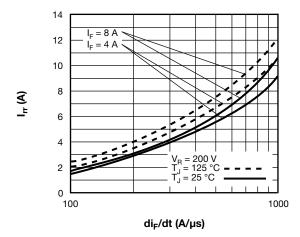


Fig. 6 - Typical Recovery Current vs. di_F/dt

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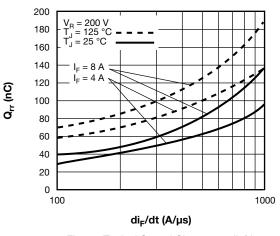


Fig. 7 - Typical Stored Charge vs. di_F/dt

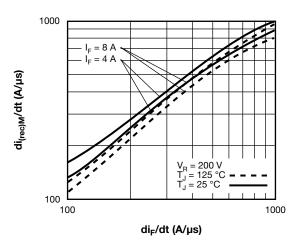
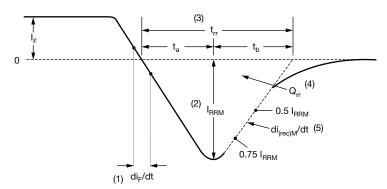


Fig. 8 - Typical di_{(rec)M}/dt vs. di_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{rr}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

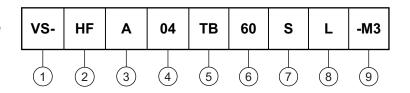
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Process designator: A = electron irradiated

Current rating (04 = 4 A)

5 - Package outline (TB = TO-220, 2 leads)

- Voltage rating (60 = 600 V)

7 - $S = D^2PAK (TO-263AB)$

- • None = tube (50 pieces)

• L = tape and reel (left oriented)

• R = tape and reel (right oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE OR TAPE AND REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA04TB60S-M3	50	1000	Antistatic plastic tube					
VS-HFA04TB60SL-M3	800	800	13" diameter reel					
VS-HFA04TB60SR-M3	800	800	13" diameter reel					

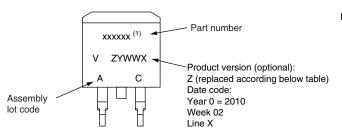
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



Part Marking Information

Vishay Semiconductors

D²PAK



Example: This is a xxxxxx ⁽¹⁾ with assembly lot code AC, assembled on WW 02, 2010

Note

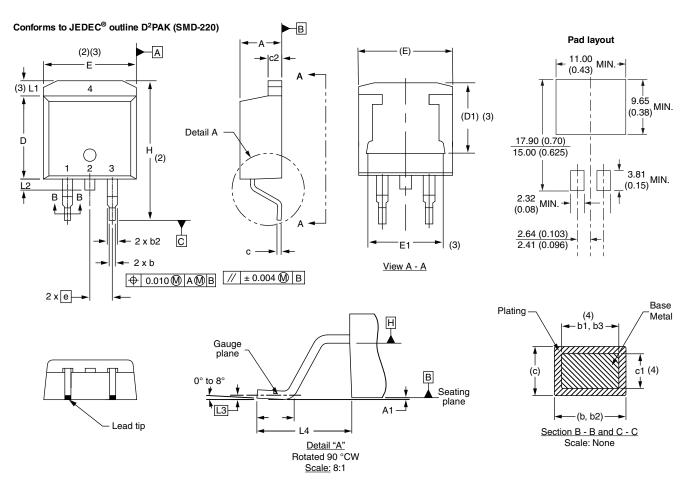
(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION				
А	Termination lead (Pb)-free				
В	Totally lead (Pb)-free				
E	RoHS-compliant and termination lead (Pb)-free				
F	RoHS-compliant and totally lead (Pb)-free				
M	Halogen-free, RoHS-compliant, and termination lead (Pb)-free				
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free				
G Green					



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES SYMBOL -	MILLIM	ETERS	INC	HES	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

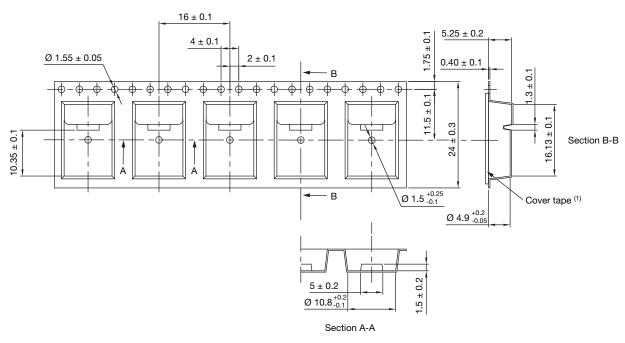
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

D²PAK (TO-263AB)

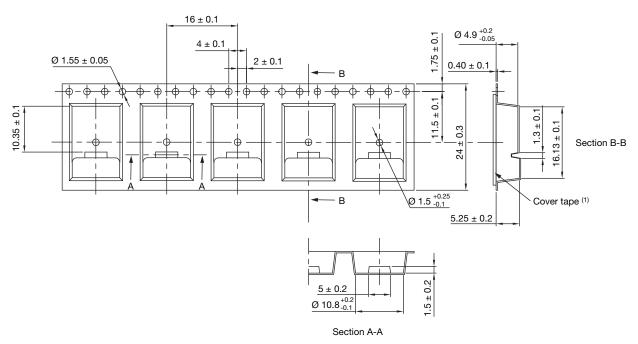
CARRIER TAPE FOR TAPE AND REEL LEFT in millimeters



Note

(1) For dimensions, see next pages

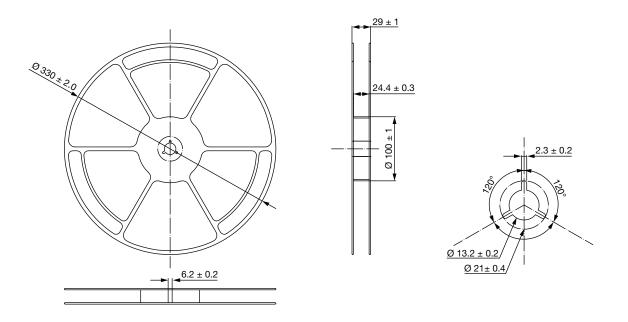
CARRIER TAPE FOR TAPE AND REEL RIGHT in millimeters



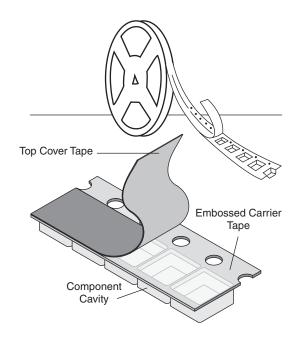
Note

(1) For dimensions, see next pages

REEL FOR CARRIER TAPE in millimeters



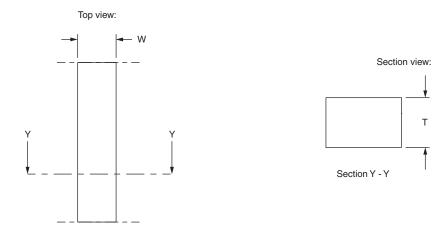
CARRIER TAPE AND REEL PACKAGING D²PAK (TO-263AB)



Packaging Information

Vishay Semiconductors

COVER TAPE FOR CARRIER TAPE in millimeters



APPLICATION	COVER TAPE WIDTH W	COVER TAPE THICKNESS T	CARRIER TAPE WIDTH	MATERIAL
D ² PAK (TO-263AB)	21.3 ± 0.1	0.060 ± 0.01	24	Antistatic/treated/transparent/polyester



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